N- and P-Channel 60V (D-S) Power MOSFET

FEATURES

- Low $R_{DS(ON)}$ to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

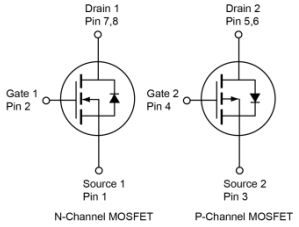
- DC-DC Converters
- Power Routing
- Motor Drives

KEY PERFORMANCE PARAMETERS

PARAMETER		TYPE	VALUE	UNIT
V_{DS}		N-ch	60	V
		P-ch	-60	
$R_{DS(on)}$ (max)	V_{GS} = 10V	N-ch	34	mΩ
	V_{GS} = 4.5V		40	
	V_{GS} = -10V	P-ch	68	
	V_{GS} = -4.5V		110	
Q_g		N-ch	10.3	nC
		P-ch	9.5	

Pb-Free RoHS COMPLIANT HALOGEN FREE

PDFN56 Dual



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

PARAMETER		SYMBOL	N-ch	P-ch	UNIT
Drain-Source Voltage		V_{DS}	60	-60	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current (Note 1)	T_C = 25°C	I_D	24	-18	A
	T_A = 25°C		5.4	-4	
Pulsed Drain Current		I_{DM}	96	-72	A
Single Pulse Avalanche Current (Note 2)		I_{AS}	12.7	-12.7	A
Single Pulse Avalanche Energy (Note 2)		E_{AS}	24	24	mJ
Total Power Dissipation	T_C = 25°C	P_D	40	40	W
	T_C = 125°C		8.1	8.1	
Total Power Dissipation	T_A = 25°C	P_D	2	2	W
	T_A = 125°C		0.4	0.4	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150		°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Thermal Resistance – Junction to Case	$R_{\Theta JC}$	3.1	°C/W
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	61	

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)							
PARAMETER	**CONDITIONS**	**SYMBOL**	**TYPE**	**MIN**	**TYP**	**MAX**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	BV_{DSS}	N-ch	60	--	--	V
	V_{GS} = 0V, I_D = -250μA		P-ch	-60	--	--	
Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	$V_{GS(TH)}$	N-ch	1.2	1.7	2.5	V
	V_{GS} = V_{DS}, I_D = -250μA		P-ch	-1.2	-1.5	-2.5	
Gate-Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	I_{GSS}	N-ch	--	--	±100	nA
	V_{GS} = ±20V, V_{DS} = 0V		P-ch	--	--	±100	nA
Drain-Source Leakage Current	V_{GS} = 0V, V_{DS} = 60V	I_{DSS}	N-ch	--	--	1	μA
	V_{GS} = 0V, V_{DS} = 60V T_J = 125°C			--	--	100	
	V_{GS} = 0V, V_{DS} = -60V		P-ch	--	--	-1	
	V_{GS} = 0V, V_{DS} = -60V T_J = 125°C			--	--	-100	
Drain-Source On-State Resistance (Note 3)	V_{GS} = 10V, I_D = 5.4A	$R_{DS(on)}$	N-ch	--	28	34	mΩ
	V_{GS} = 4.5V, I_D = 4.9A			--	33	40	
	V_{GS} = -10V, I_D = -4A		P-ch	--	57	68	
	V_{GS} = -4.5V, I_D = -3.2A			--	73	110	
Forward Transconductance (Note 3)	V_{DS} = 5V, I_D = 5.4A	g_{fs}	N-ch	--	19	--	S
	V_{DS} = -5V, I_D = -4A		P-ch	--	11	--	
Dynamic (Note 4)							
Total Gate Charge	N-ch V_{DS} = 30V, I_D = 5.4A P-ch V_{DS} = -30V, I_D = -4A	$Q_{g(VGS=10V)}$	N-ch	--	20.8	--	nC
		$Q_{g(VGS=-10V)}$	P-ch	--	18.1	--	
Total Gate Charge	N-ch V_{DS} = 30V, I_D = 4.9A P-ch V_{DS} = -30V, I_D = -3.2A	$Q_{g(VGS=4.5V)}$	N-ch	--	10.3	--	
		$Q_{g(VGS=-4.5V)}$	P-ch	--	9.5	--	
Gate-Source Charge		Q_{gs}	N-ch	--	3.9	--	
			P-ch	--	2.6	--	
Gate-Drain Charge		Q_{gd}	N-ch	--	4.2	--	
			P-ch	--	4.8	--	
Input Capacitance	N-ch V_{GS} = 0V, V_{DS} = 30V f = 1.0MHz P-ch V_{GS} = 0V, V_{DS} = -30V f = 1.0MHz	C_{iss}	N-ch	--	1159	--	pF
			P-ch	--	930	--	
Output Capacitance		C_{oss}	N-ch	--	59	--	
			P-ch	--	65	--	
Reverse Transfer Capacitance		C_{rss}	N-ch	--	15	--	
			P-ch	--	26	--	
Gate Resistance	f = 1.0MHz	R_g	N-ch	0.6	2	4	Ω
			P-ch	4.5	15	30	

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)							
PARAMETER	**CONDITIONS**	**SYMBOL**	**TYPE**	**MIN**	**TYP**	**MAX**	**UNIT**
Switching (Note 4)							
Turn-On Delay Time	N-ch V_{GS} = 10V, V_{DS} = 30V, I_D = 5.4A, R_G = 2Ω P-ch V_{GS} = -10V, V_{DS} = -30V, I_D = -4A, R_G = 2Ω	$t_{d(on)}$	N-ch	--	7.4	--	ns
			P-ch	--	4	--	
Turn-On Rise Time		t_r	N-ch	--	25	--	
			P-ch	--	28	--	
Turn-Off Delay Time		$t_{d(off)}$	N-ch	--	18	--	
			P-ch	--	44	--	
Turn-Off Fall Time		t_f	N-ch	--	18	--	
			P-ch	--	44	--	
Source-Drain Diode							
Forward Voltage (Note 3)	V_{GS} = 0V, I_S = 5.4A	V_{SD}	N-ch	--	--	1	V
	V_{GS} = 0V, I_S = -4A		P-ch	--	--	-1	
Reverse Recovery Time	N-ch I_S = 5.4A, dI/dt = 100A/μs P-ch I_S = -4A, dI/dt = 100A/μs	t_{rr}	N-ch	--	16	--	ns
			P-ch	--	13	--	
Reverse Recovery Charge		Q_{rr}	N-ch	--	11	--	nC
			P-ch	--	7.8	--	

Notes:

1. Silicon limited current only.
2. N-ch : L = 0.3mH, V_{GS} = 10V, V_{DD} = 25V, R_G = 25Ω, I_{AS} = 12.7A, Starting T_J = 25°C
   P-ch : L = 0.3mH, V_{GS} = -10V, V_{DD} = -25V, R_G = 25Ω, I_{AS} = -12.7A, Starting T_J = 25°C
3. Pulse test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
4. Switching time is essentially independent of operating temperature.

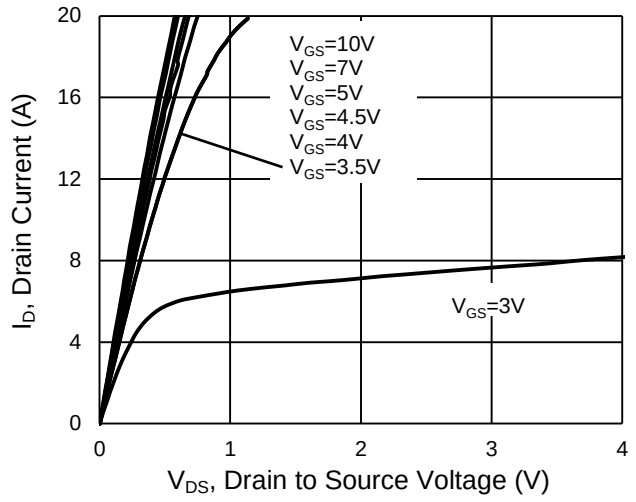
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM6502CR RLG	PDFN56 Dual	2,500pcs / 13” Reel

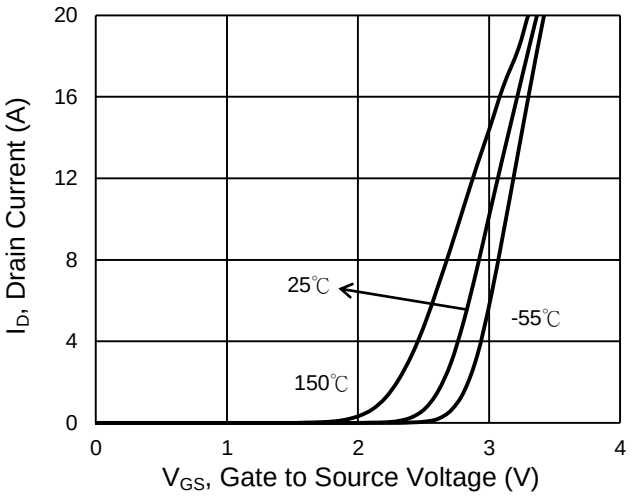
CHARACTERISTICS CURVES (N-Channel)

(T_A = 25°C unless otherwise noted)

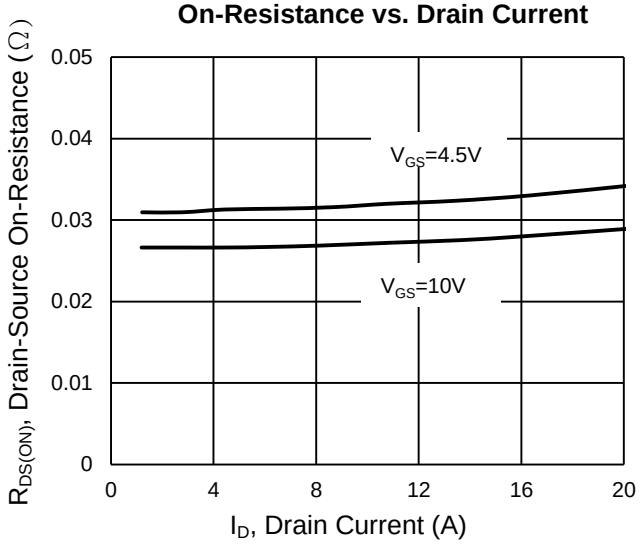
Output Characteristics



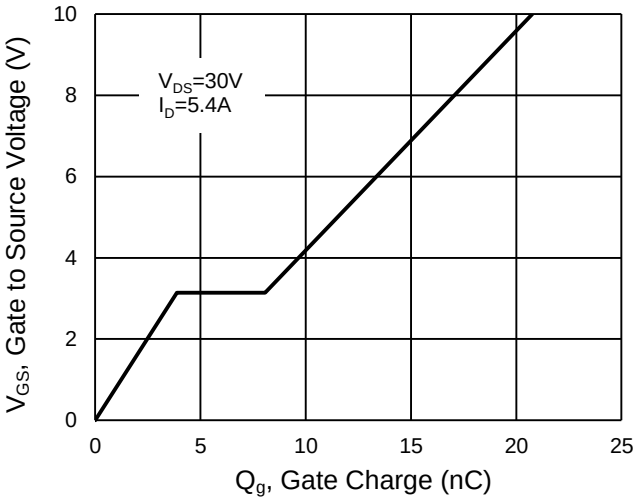
Transfer Characteristics



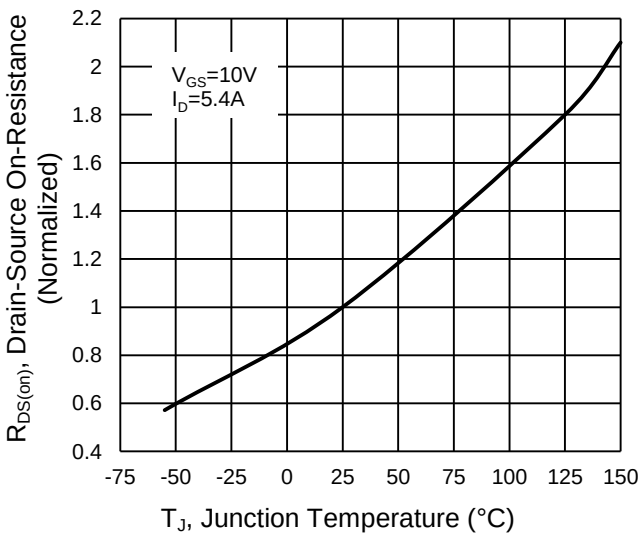
On-Resistance vs. Drain Current



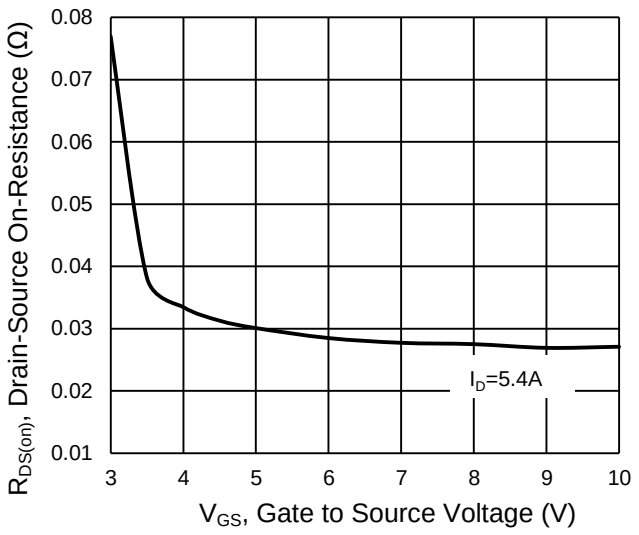
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



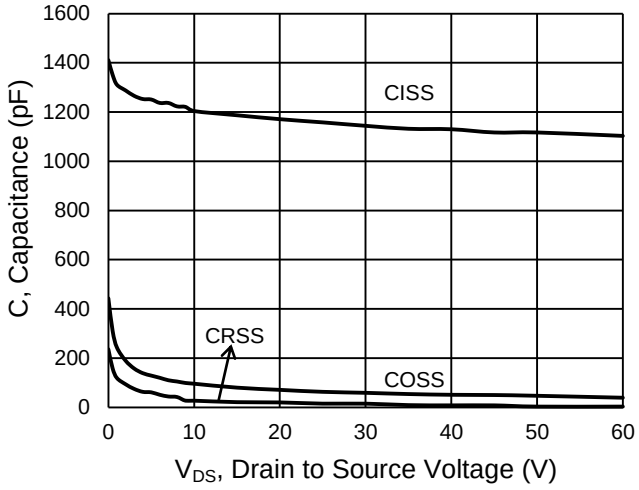
On-Resistance vs. Gate-Source Voltage



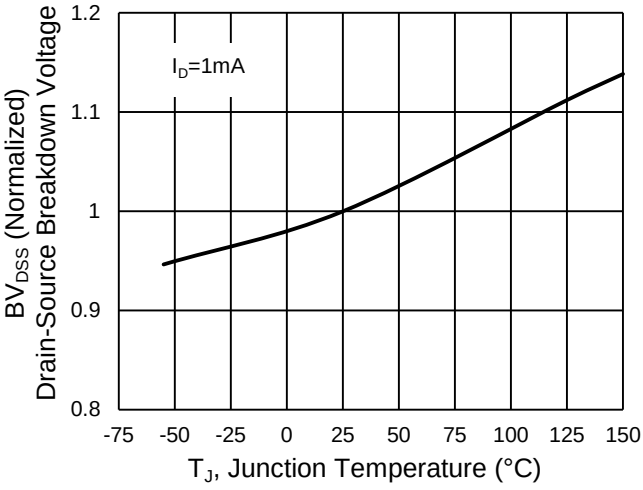
CHARACTERISTICS CURVES (N-Channel)

(T_A = 25°C unless otherwise noted)

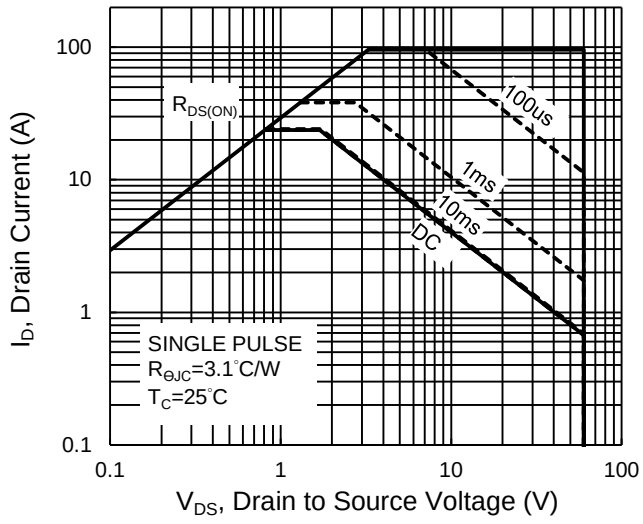
Capacitance vs. Drain-Source Voltage



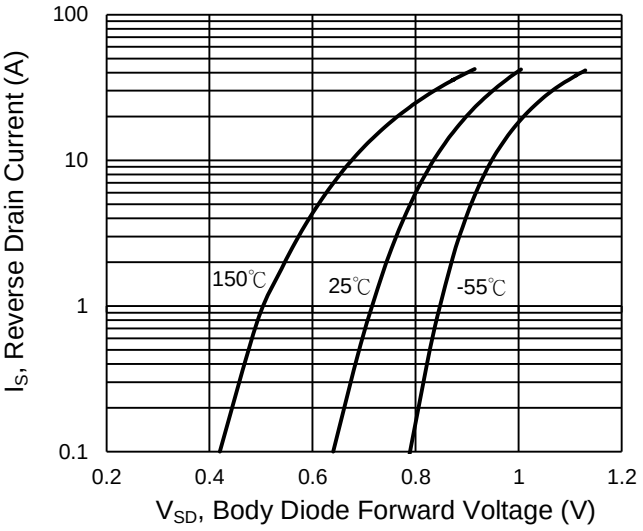
BV_{DSS} vs. Junction Temperature



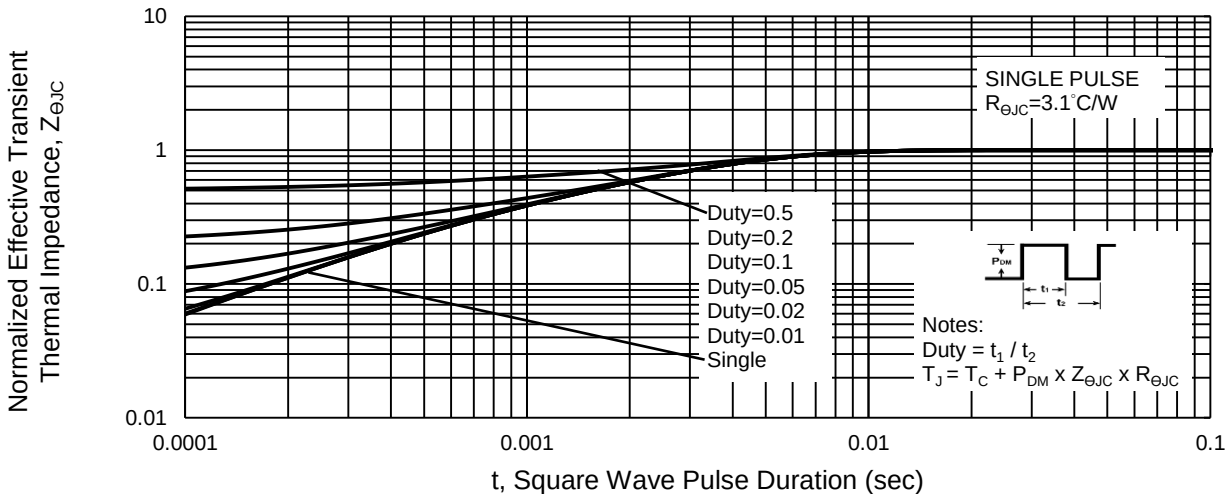
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



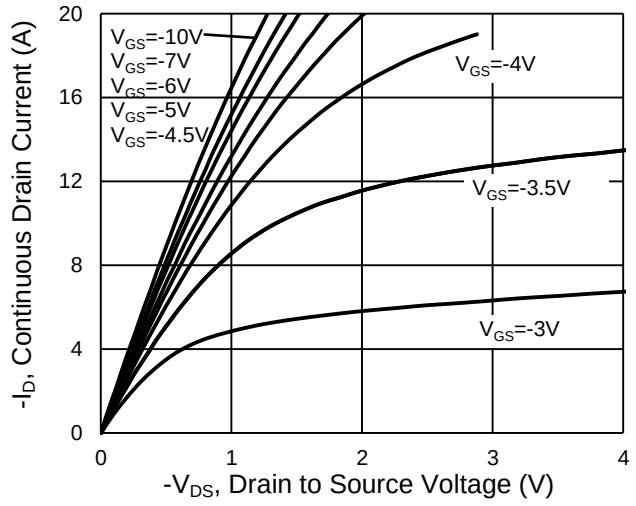
Normalized Thermal Transient Impedance, Junction-to-Case



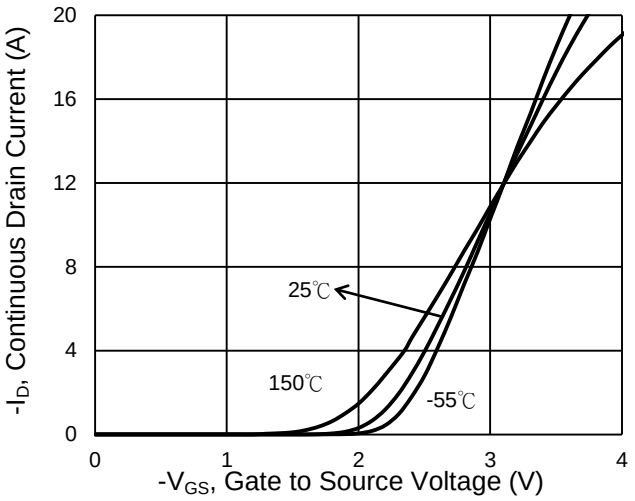
CHARACTERISTICS CURVES (P-Channel)

(T_A = 25°C unless otherwise noted)

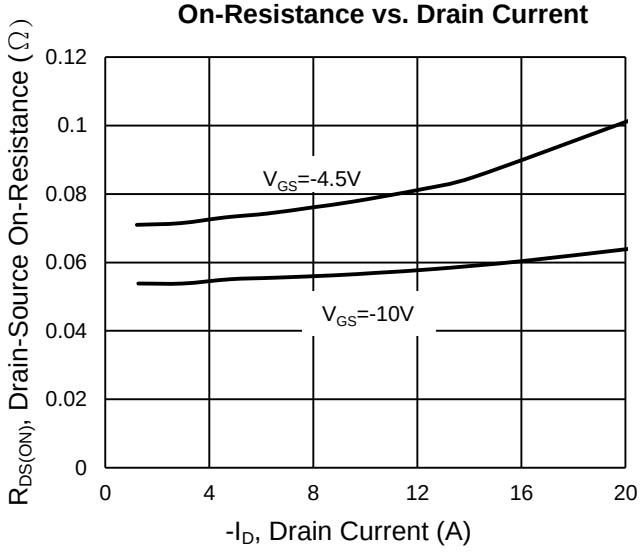
Output Characteristics



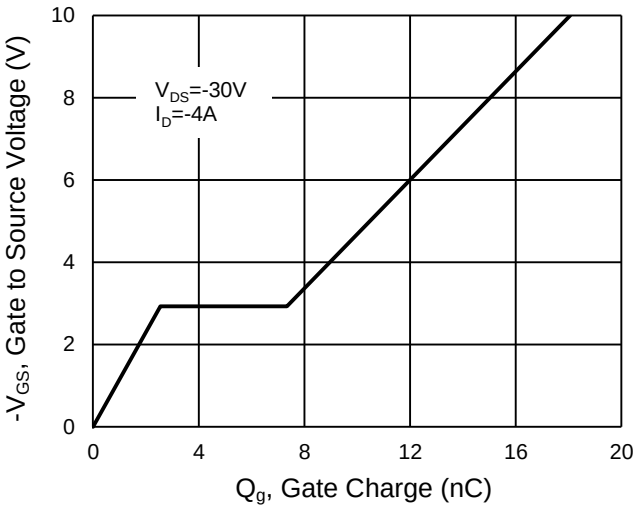
Transfer Characteristics



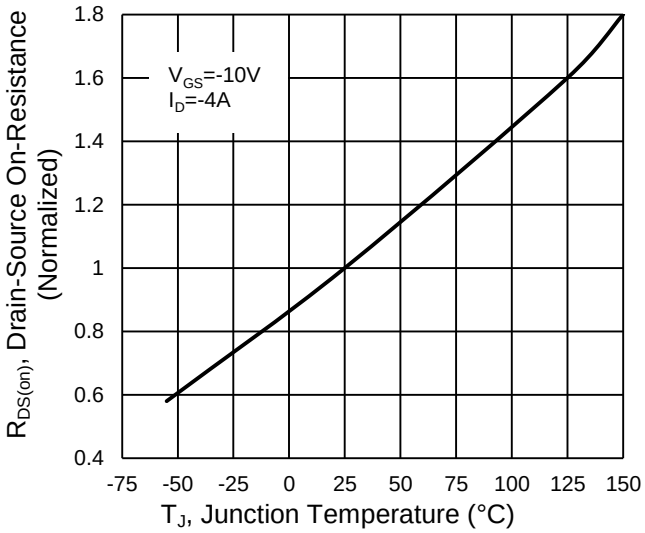
On-Resistance vs. Drain Current



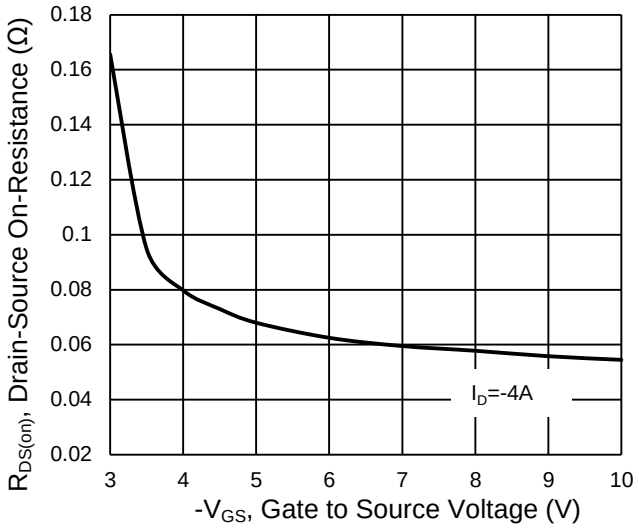
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



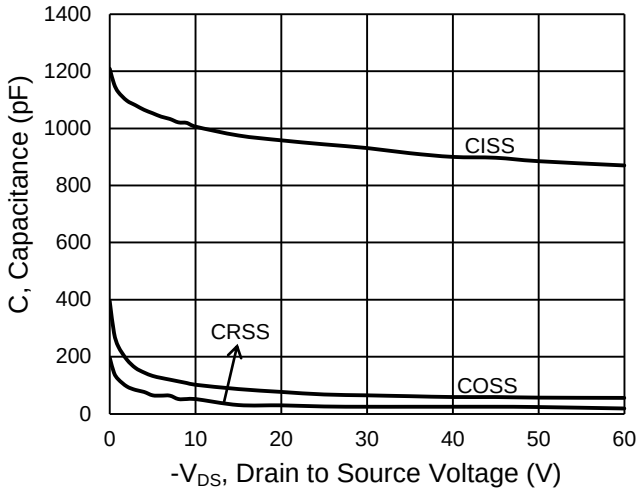
On-Resistance vs. Gate-Source Voltage



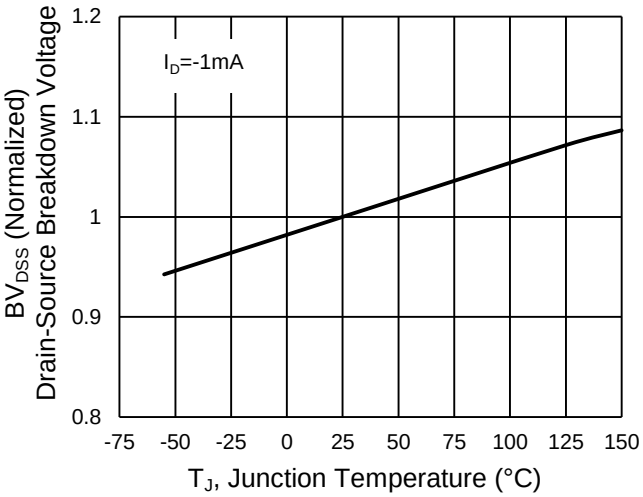
CHARACTERISTICS CURVES (P-Channel)

(T_A = 25°C unless otherwise noted)

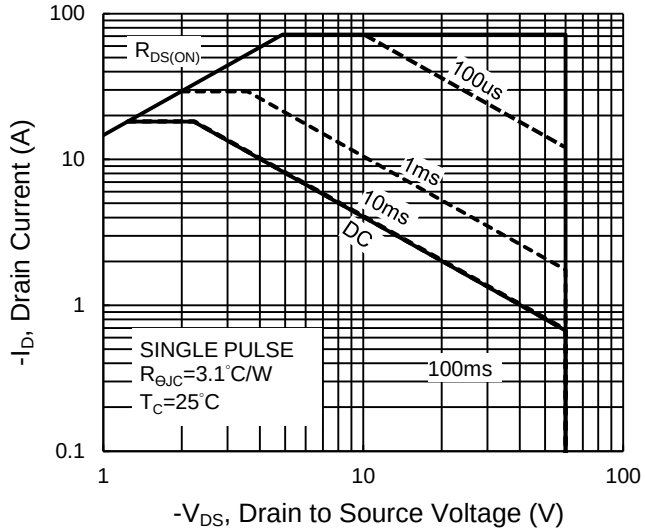
Capacitance vs. Drain-Source Voltage



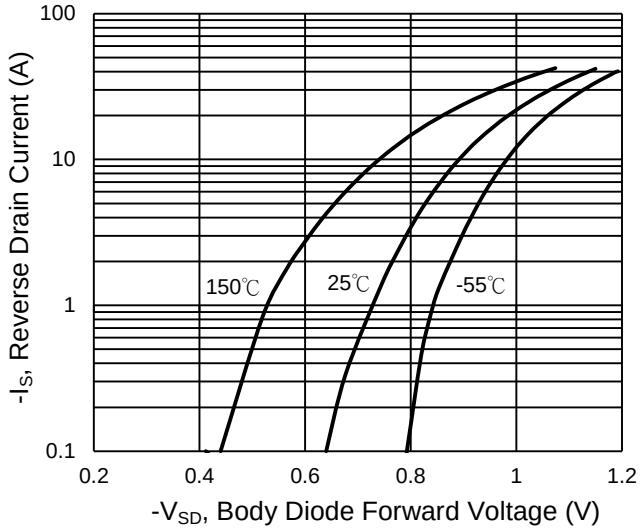
BV_{DSS} vs. Junction Temperature



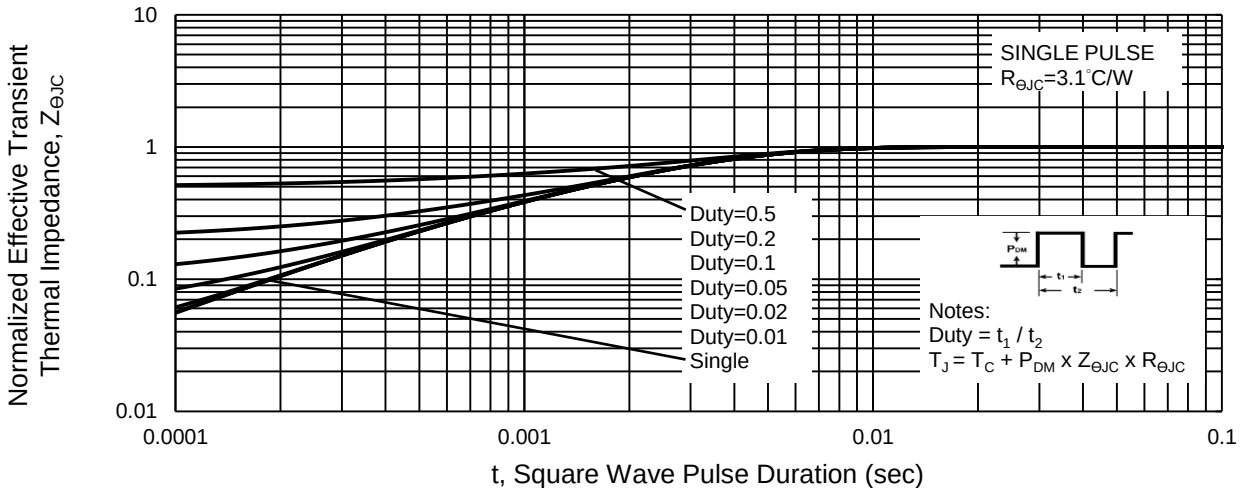
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

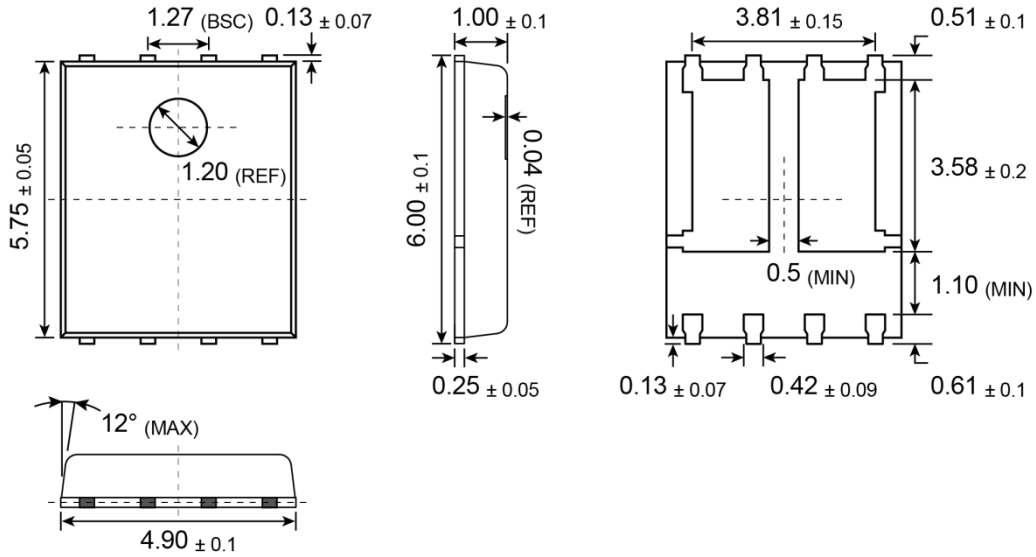


Normalized Thermal Transient Impedance, Junction-to-Case

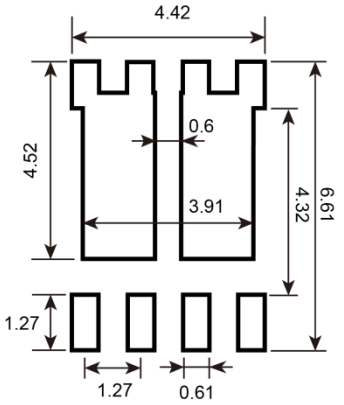


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

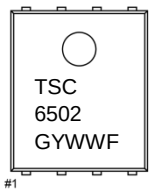
PDFN56 Dual



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



G = Halogen Free
Y = Year Code
WW = Week Code (01~52)
F = Factory Code

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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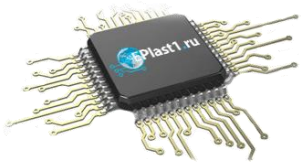
- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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